

Pro Electron Surface Mount Bipolar Devices (continued)

Device No. (SOT-23 Mark)	Case Style	V _{CES} [*]		V _{CEO}		V _{EBO}		I _{CES} [*]		I _{hFE}		I _C & V _{CE}		V _{CE(SAT)} (V) & V _{BE(SAT)} (V)		V _{BE(SAT)} [*] V _{BE(ON)} (V)		I _C (mA)	C _{ob} (pF) Max	f _T (MHz) @ I _C (mA)		NF (dB) Max	Test Conditions	Process No.
		V _{CBO} (V) Min	V _{CE0} (V) Min	V _{CE0} (V) Min	V _{EBO} (V) Min	I _{CBO} (nA) Max	I _{hFE} Min	I _{hFE} Max	I _C (mA) Max	V _{CE} (V) Max	V _{CE(SAT)} (V) Max	V _{BE(SAT)} (V) Min	V _{BE(ON)} (V) Max	I _C (mA) Max	f _T Min	f _T Max								
BC859C (4C)	TO-236 (49)	30	30	5	30	15	30	5	800	2	5	0.65	100					4	(Note 1)	68				
BC860C (4G)	TO-236 (49)	50	45	5	30	15	30	5	800	2	5	0.3 0.65	10 100					3	(Note 1)	68				
BCP52	TO-261 (47)	60	60	5	30	100	30	5	25 40	5 250	2	0.5	*1 500							78 (6-28)				
BCP63	TO-261 (47)	100	80	5	30	100	30	5	25 40	5 250	2	0.5	*1 500							78				
BCP54	TO-261 (47)	45	45	5	30	100	30	5	25 40	5 250	2	0.5	*1 500							38 (6-32)				
BCP55	TO-261 (47)	60	60	5	30	100	30	5	25 40	5 250	2	0.5	*1 500							38				
BCP56	TO-261 (47)	100	80	5	30	100	30	5	25 40	5 250	2	0.5	*1 500							38				
BCV26 (FD)	TO-236 (49)	40	30	10	30	100	30	1	4,000 10,000 20,000	5 10 100	5	1	1.5 100							61 (6-35)				
BCV27 (FF)	TO-236 (49)	40	30	10	30	100	30	1	4,000 10,000 20,000	5 10 100	5	1	1.5 100							05 (6-39)				
BCV71 (KT)	TO-236 (49)	80	60	5	20	100	20	2	110	220	5	0.25	10					10	(Note 1)	10				
BCV72 (KB)	TO-236 (49)	80	60	5	20	100	20	2	200	450	5	0.25	10					10	(Note 1)	10				
BCW30 (C2)	TO-236 (49)	32	32	5	32	100	32	0.01	215	500	5	0.3	10					10	(Note 1)	68				
BCW31 (D1)	TO-236 (49)	32	32	5	32	100	32	0.01	150	270	5	0.25	10					10	(Note 1)	10				

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.